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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent application of)
Shunpei YAMAZAKI et al.)
Serial No. 09/436,984) Art Unit: 2823
Filed: November 9, 1999) Examiner: W. Coleman
For: SEMICONDUCTOR DEVICE AND)
MANUFACTURING METHOD THEREOF) Date: February 13, 2002

Handwritten signatures and initials:
#17
W. Coleman
3/22/02

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows.

IN THE CLAIMS:

Please add new claims 32-54 as follows:

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OFFICE OF PETITIONS

--32. A semiconductor device comprising:

- a semiconductor film formed on an insulating surface;
- a channel forming region in the semiconductor film;
- a gate insulating film formed on the semiconductor film;
- a gate electrode formed over the channel forming region with the gate insulating film interposed therebetween;
- a pair of side walls adjacent to side surfaces of the gate electrode;
- a pair of first impurity regions doped with an N-type impurity at a first concentration and formed in the semiconductor film with the channel forming region extending therebetween wherein the pair of side walls overlap the pair of first impurity regions; and
- a pair of second impurity regions doped with an N-type impurity at a second concentration greater than the first concentration and formed in the semiconductor film adjacent to the pair of first impurity regions; and